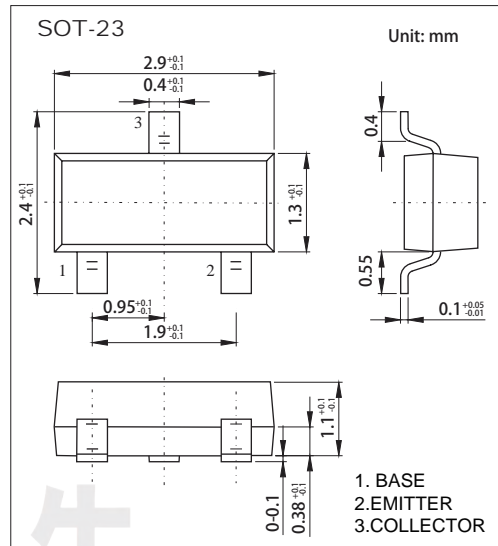


Transistor

NPN Transistors 2SC945

■ Features

- Excellent hFE Linearity
- Low noise
- Complementary to 2SA733



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	60	V
Collector - Emitter Voltage	V _{CE0}	50	
Emitter - Base Voltage	V _{EB0}	5	
Collector Current - Continuous	I _c	150	mA
Collector Power Dissipation	P _c	200	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	

Transistor

NPN Transistors 2SC945

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	VCBO	Ic= 100 μ A, IE=0	60			V
Collector- emitter breakdown voltage	VCEO	Ic= 1 mA, IB=0	50			
Emitter - base breakdown voltage	VEBO	IE= 100 μ A, IC=0	5			
Collector cut-off current	ICBO	VCB= 60 V, IE=0			0.1	μ A
Collector cut-off current	ICER	VCE= 55 V, R=10M Ω			0.1	
Emitter cut-off current	IEBO	VEB= 5V, IC=0			0.1	
Collector-emitter saturation voltage	VCE(sat)	Ic=100 mA, IB= 10mA			0.3	V
Base - emitter saturation voltage	VBE(sat)	IC=100 mA, IB= 10mA			1	
DC current gain	hFE(1)	VCE= 6V, Ic= 1mA	130		400	
	hFE(2)	VCE= 6V, Ic= 0.1mA	40			
Noise figure	NF	VCE=6V,Ic=0.1mA Rg=10k Ω ,f=1kMHZ			10	dB
Collector output capacitance	Cob	VCB=10V,IE=0,f=1MHZ			3	pF
Transition frequency	ft	VCE= 6V, Ic= 10mA,f=30MHZ	150			MHz

■ Classification of hFE(1)

Rank	L	H
Range	130-200	200-400
Marking	CR •	

NPN Transistors 2SC945

Typical Characteristics

